

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. - 4. (Canceled)

5. (Previously Presented) A manufacturing method of a large-diameter SiC wafer comprising the steps of:

placing a small diameter α -SiC single crystal wafer on a graphite plate;

forming a film of polycrystal SiC around an outer circumference of said wafer by depositing polycrystal SiC over the graphite plate and over a surface of the α -SiC single crystal wafer;

grinding the polycrystal SiC on the surface of the α -SiC single crystal wafer to manufacture an increased-diameter SiC of a double structure in which the polycrystal SiC plate portion is planarly formed around an outer circumference of the small-diameter α -SiC single crystal wafer; and

wherein a top and bottom surface of the small diameter α -SiC single crystal wafer is free of the polycrystal SiC.

6. (Previously Presented) The manufacture method according to claim 5, further comprising:

masking the α -SiC single crystal wafer with a mask;

depositing the polycrystal SiC over the graphite plate on the mask; and

removing the mask in the grinding, thereby forming the large-diameter SiC wafer.

7. (Canceled)